

LISTING OF THE CURRENT CLAIMS
IN ACCORDANCE WITH REVISED AMENDMENT PRACTICE

1. (Currently Amended) A physical vapor deposition target consisting of:
greater than or equal to 90 atomic percent copper;
a first added element, wherein the first added element is Sn; and
a second added element selected from the group consisting of Al, As, Au, B,
[[Be, Ca,]] Cd, Co, Fe, Ga, Ge, Hf, Hg, Ir, Li, Mg, [[Mn, Nb,]] Ni, Pb, Pd, Pt, [[Sb,]]
Sc, Si, [[Ta, Te,]] V[[,]] and W[[, and Zn]].
2. (Original) The physical vapor deposition target of claim 1 wherein a total
combined amount of the first and second added elements present in the target is
from at least 100 ppm to less than about 10 atomic %.

Claim 3: Canceled.

4. (Original) The physical vapor deposition target of claim 1 wherein the first and
second added elements are each present in the target at 0.5 atomic percent.

Claim 5: Canceled.

6. (Original) The physical vapor deposition target of claim 1 wherein the first and
second added elements are present in the target in equivalent atomic percent
relative to each other.

Claims 7-11: Canceled.

12. (Currently Amended) The physical vapor deposition target of claim [[11]] 1
wherein the total amount of the at least two elements is from about 1000 ppm to
less than about 1 atomic percent.

Claims 13-32: Canceled.

33. (New) A physical vapor deposition target consisting of:
greater than or equal to 90 atomic percent copper;
a first added element, wherein the first added element is Ag; and
a second added element selected from the group consisting of As, B, Be, Ca, Cd, Fe, Ga, Ge, Hf, Hg, In, Ir, Li, Mg, Mn, Nb, Pb, Sb, Sc, Te, V, W and Zn.
34. (New) The physical vapor deposition target of claim 33, wherein a total combined amount of the first and second added elements present in the target is from at least 100 ppm to less than about 10 atomic %.
35. (New) The physical vapor deposition target of claim 33, wherein the first and second added elements are present in the target in equivalent atomic percent relative to each other.
36. (New) A physical vapor deposition target consisting of:
greater than or equal to 90 atomic percent copper;
a first added element, wherein the first added element is Ag; and
a second added element selected from the group consisting of As, B, Be, Ca, Cd, Fe, Ga, Ge, Hf, Hg, In, Ir, Li, Mg, Mn, Nb, Pb, Sb, Sc, Te, V, W and Zn; and
a third added element selected from the group consisting of As, B, Be, Ca, Cd, Fe, Ga, Ge, Hf, Hg, In, Ir, Li, Mg, Mn, Nb, Pb, Sb, Sc, Te, V, W and Zn, wherein the third added element is different from the second added element.
37. (New) The physical vapor deposition target of claim 36, wherein a total combined amount of the first, second and third added elements present in the target is from at least 100 ppm to less than about 10 atomic %.
38. (New) The physical vapor deposition target of claim 36, wherein the first, second and third added elements are present in the target in equivalent atomic percent relative to each other.